

MOSFETs Silicon N-channel MOS (U-MOSIV)

TK18E10K3

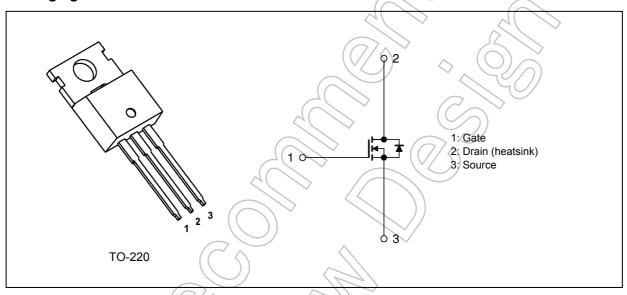
1. Applications

· Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 33 \text{ m}\Omega$ (typ.)
- (2) High forward transfer admittance: $|Y_{fs}| = 28 \text{ S (typ.)}$
- (3) Low leakage current: I_{DSS} = 10 μA (max) (V_{DS} = 100 V)
- (4) Enhancement mode: V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_{D} = 1 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25°C unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage	7/	V_{DSS}	100	V
Drain-gate voltage (R _{GS} = 20 kg	Ω)	V_{DGR}	100	
Gate-source voltage		V_{GSS}	±20	
Drain current (DC)	(Note 1)	I _D	18	Α
Drain current (pulsed)	(Note 1)	I _{DP}	54	
Power dissipation (T _c = 25°C	;)	P _D	71	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	28	mJ
Avalanche current		I _{AR}	18	Α
Repetitive avalanche energy	(Note 3)	E _{AR}	7.1	mJ
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance		1.76	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	83.3	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 25 V, T_{ch} = 25°C (initial), L = 0.14 mH, R_G = 25 Ω , I_{AR} = 18 A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μΑ
Drain cut-off current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V	7	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	100	_		V
Drain-source breakdown voltage	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	65) /~		
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	/_	4.0	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 9 A	$\langle \cdot \rangle$	33	42	mΩ
Forward transfer admittance	Y _{fs}	V _{DS} = 10 V, I _D = 9 A		28		S

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	-/-	1580	> —	pF
Reverse transfer capacitance	C _{rss}		> -((135	_	
Output capacitance	C _{oss}		(-)	200	/ —	
Switching time (rise time)	t _r	See Figure 6.2.1.	7-	> 9	_	ns
Switching time (turn-on time)	t _{on}	$\mathcal{A}(\mathcal{A})$		21		
Switching time (fall time)	t _f			7	_	
Switching time (turn-off time)	t _{off}		\cap	30	_	

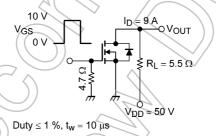


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 80 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 18 \text{ A}$		33	_	nC
Gate-source charge	Q_{gs}		_	20	_	
Gate-drain charge	Q _{gd}		_	13	_	

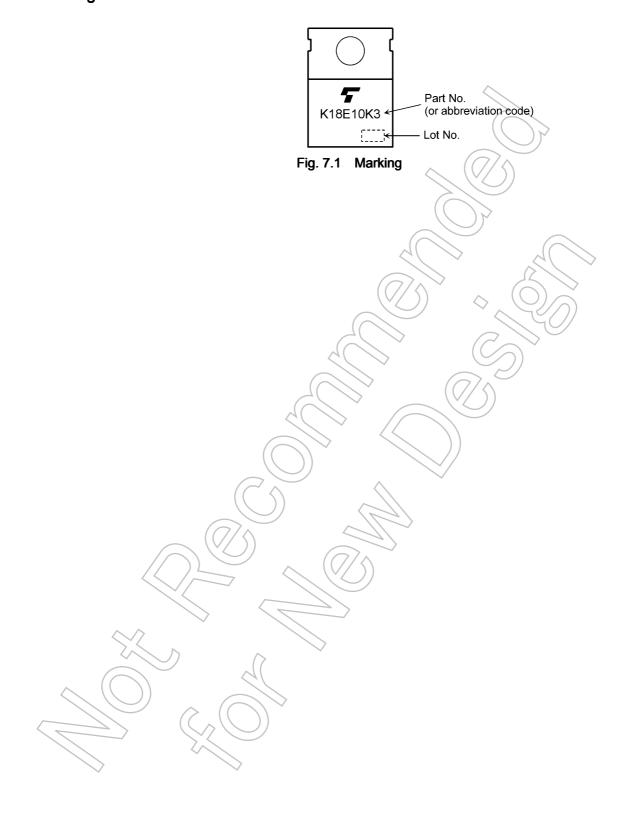
6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 4)	I _{DR}	_	_	_	18	Α
Reverse drain current (pulsed)	(Note 4)	I _{DRP}	_			54	
Diode forward voltage		V_{DSF}	I _{DR} = 18 A, V _{GS} = 0 V	_	_	-1.2	V
Reverse recovery time		t _{rr}	I _{DR} = 18 A, V _{GS} = 0 V		53	_	ns
Reverse recovery charge		Q_{rr}	-dl _{DR} /dt = 50 A/μs	_	58	_	nC

Note 4: Ensure that the channel temperature does not exceed 150°C.



7. Marking



8. Characteristics Curves (Note)

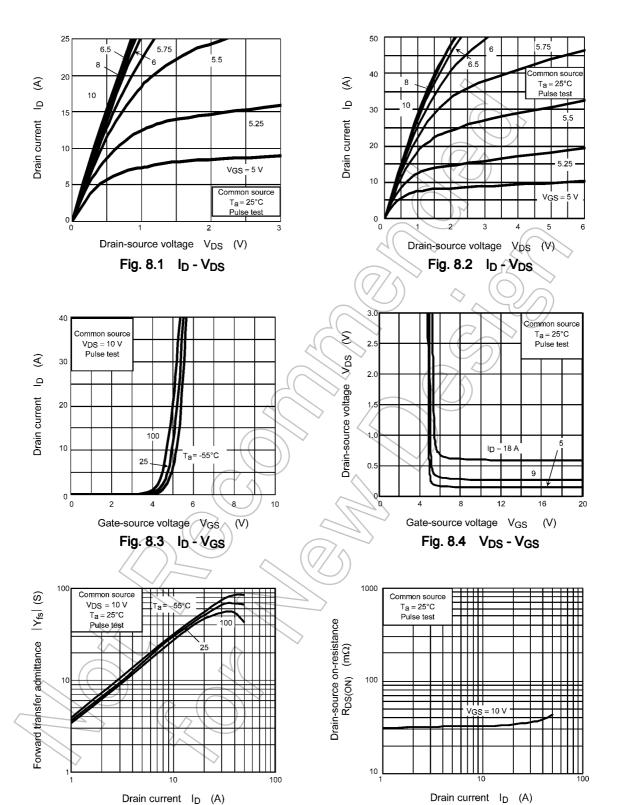


Fig. 8.6 R_{DS(ON)} - I_D

Fig. 8.5 |Y_{fs}| - I_D

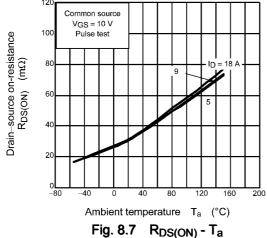


FIG. 6.7 KDS(ON) - 1a

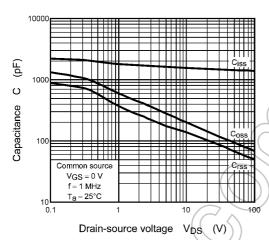


Fig. 8.9 Capacitance - V_{DS}

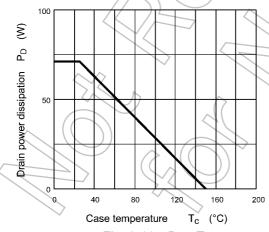


Fig. 8.11 P_D - T_c (Guaranteed Maximum)

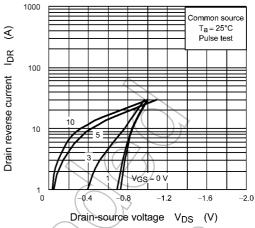


Fig. 8.8 IDR - VDS

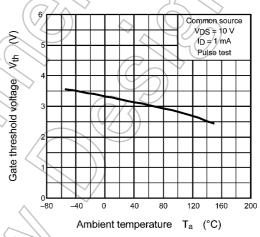


Fig. 8.10 V_{th} - T_a

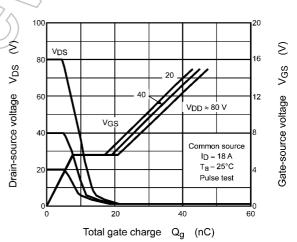
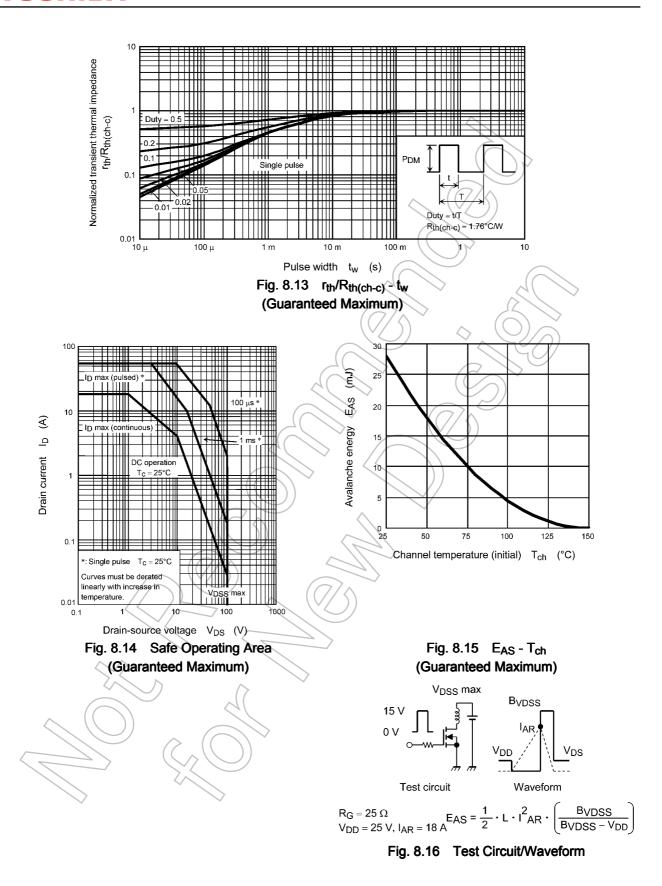


Fig. 8.12 Dynamic Input/Output Characteristics

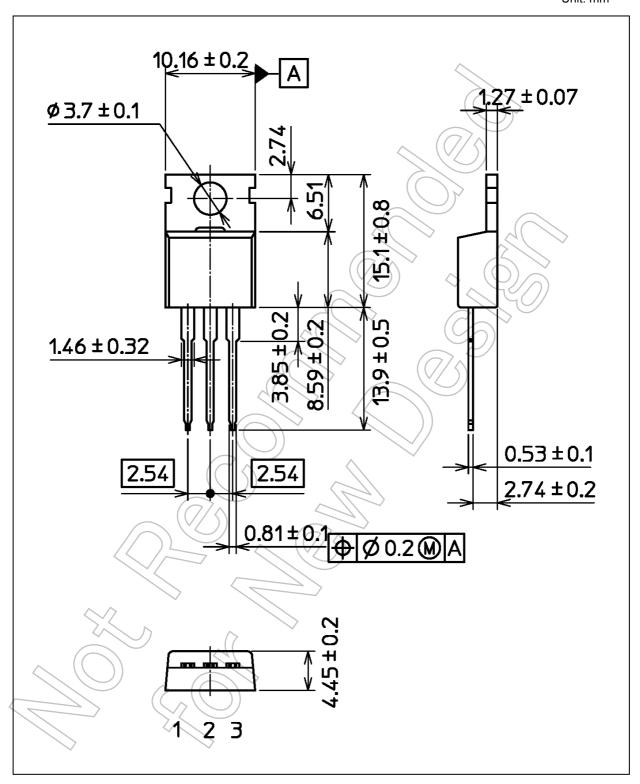


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 1.93 g (typ.)

Package Name(s)
TOSHIBA: 2-10X1A
Nickname: TO-220



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